## NSN 5961-01-539-0282

**Fiig:** A110a0

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-539-0282 **Inclosure Material:** Plastic **Overall Length:** 2.350 inches **Overall Diameter:** 0.350 inches **Mounting Method: Terminal Semiconductor Material:** Lead sulfide Voltage Rating In Volts Per Characteristic: 400.00 reverse voltage, dc and 400.00 repetitive peak reverse voltage and 400.00 working peak reverse voltage **Current Rating Per Characteristic:** 0.30 amperes source cutoff current absolute or 0.80 amperes collector current, dc and 60.00 amperes forward current, dc nanoamperes **Capacitance Rating In Picofarads:** 280.0 **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** 10 amp, diffused junction, high current capability and low forward voltage drop, surge overload rating to 600a peak, low reverse leakage current **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No